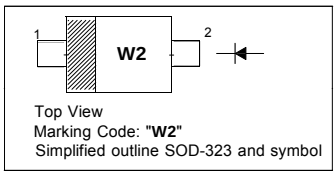
Silicon Epitaxial Planar Switching Diode

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode



Top View
Marking Code: "**W2**"
Simplified outline SOD-323 and symbol

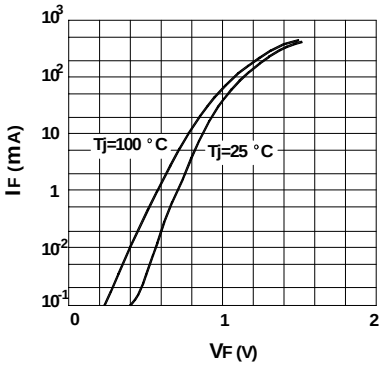
Absolute Maximum Ratings (T_a = 25 °C)

Parameter	Symbol	Value	Unit
Repetitive Reverse Voltage	V_{RRM}	100	V
Average Rectified Forward Current	$I_{F(AV)}$	200	mA
Non-repetitive Peak Forward Surge Current at t = 1 s at t = 1 µs	I_{FSM}	0.5 1	A
Power Dissipation	P_{tot}	200	mW
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	625	°C/W
Junction Temperature	T_j	150	°C
Storage Temperature Range	T_{stg}	- 55 to + 150	°C

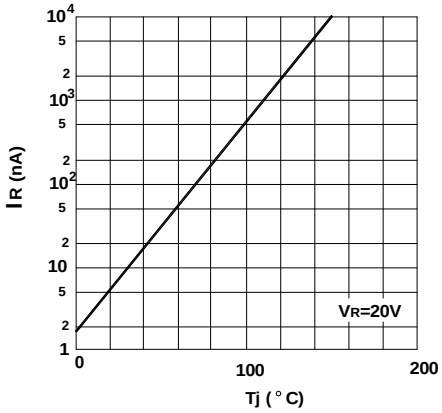
Electrical Characteristics (T_a = 25°C)

Parameter	Symbol	Min.	Max.	Unit
Forward Voltage at I_F = 10 mA	V_F	-	1	V
Reverse Breakdown Voltage at I_R = 5 µA at I_R = 100 µA	 $V_{(BR)R}$ $V_{(BR)R}$	 75 100	 - -	 V V
Reverse Current at V_R = 20 V at V_R = 75 V at V_R = 20 V, T_J = 150 °C	I_R	 - - -	 25 5 50	 nA µA µA
Total Capacitance at V_R = 0 V, f = 1 MHz	C_{tot}	-	4	pF
Reverse Recovery Time at I_F = I_R = 30 mA, R_L = 100 Ω, I_{RR} = 3 mA	t_{rr}	-	50	ns

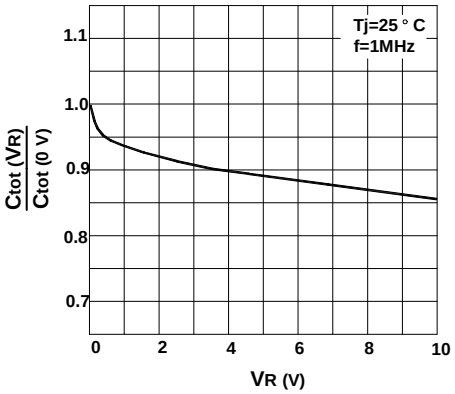
Forward characteristics



Leakage current vs. junction temperature



Reverse capacitance vs. reverse voltage



Dynamic forward resistance vs. forward current